

# isc N-Channel MOSFET Transistor

# SPW55N80C3

### **FEATURES**

- Drain Current : I<sub>D</sub>= 54.9A@ T<sub>C</sub>=25 ℃
- Drain Source Voltage
  - : V<sub>DSS</sub>= 800V(Min)
- Static Drain-Source On-Resistance
  - :  $R_{DS(on)}$  = 85m  $\Omega$  (Max) @  $V_{GS}$ = 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### **DESCRITION**

 motor drive, DC-DC converter, power switch and solenoid drive.

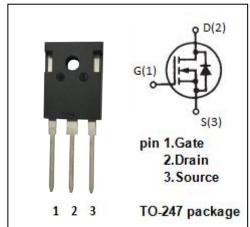
## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	800	V
$V_{GS}$	Gate-Source Voltage	±25	V
I <sub>D</sub>	Drain Current-Continuous	54.9	А
Іом	Drain Current-Single Pulsed	150	А
$P_D$	Total Dissipation @T <sub>C</sub> =25℃	500	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature	-55~150	${\mathbb C}$

#### THERMAL CHARACTERISTICS

isc website: www.iscsemi.cn

SYMBOL	PARAMETER	MAX	UNIT	
R <sub>th(J-c)</sub>	Junction-to-case thermal resistance	0.25	°C/W	



			40	10810
T - C	B -	S C		Ž
H H			G	L
•	U U	R		D
	DIM	m	nm	]
	DIN	MIN	MAX	
	Λ	10.00	24 50	1

DIM		
DIM	MIN	MAX
Α	19.80	21.50
В	15.40	15.90
С	4.70	5.30
D	0.90	1.26
F	3.50	3.90
G	2.70	3.30
Н	3.90	4.10
J	0.500	0.700
K	19.50	20.50
L	1.90	2.20
N	10.80	11.00
Q	6.00	6.30
R	2.90	3.30
S	1.80	2.20
T	2.15	2.35
W	4.90	5.10
Z	6.00	6.30

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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	Тур	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; ID =0.25mA	800	-	-	V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> ; ID =3.3mA	2.1	-	3.9	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =32.6A	-	-	85	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V	-	-	±100	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = 800V; V <sub>GS</sub> = 0V	-	-	25	μА
V <sub>SD</sub>	Diode forward voltage	Is= 54.9A, V <sub>GS</sub> = 0V	-	0.95	-	V

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